NSN 5961-01-255-7723

Semiconductor Device Set - Page 1 of 2

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Inclosure Material:

Metal all transistor

Overall Length:

1.252 inches all transistor

Overall Height:

0.250 inches all transistor and 0.340 inches all transistor

Overall Width:

0.700 inches all transistor

End Application:

1430-01-214-8306

Mounting Facility Quantity:

2 all transistor

Internal Configuration:

Junction contact all transistor

Electrode Internally-electrically Connected To Case:

Collector all transistor

Internal Junction Configuration:

Npn all transistor

Component Function Relationship:

Matched

Component Name And Quantity:

2 transistor

Mounting Method:

Unthreaded hole all transistor

Field Force Effect Type:

Electrostatic charge

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

120.0 collector to base voltage/static/emitter open all transistor and 75.0 collector to emitter voltage/static/base open all transistor and 7.0 emitter to base voltage, static, collector open all transistor

Current Rating Per Characteristic:

5.00 amperes source cutoff current all transistor and 7.00 amperes source cutoff current all transistor

Power Rating Per Characteristic:

35.0 watts small-signal input power, common-collector preset all transistor

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius ambient air all transistor

Test Data Document:

18876-11465917 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

1 case all transistor and 2 pin all transistor

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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